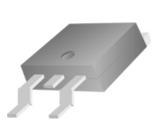
## N-Channel 60-V (D-S) MOSFET

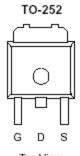
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r <sub>DS(on)</sub> provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	<b>I</b> <sub>D</sub> (A)		
60	$38 @ V_{GS} = 10V$	30		
00	$50 @ V_{GS} = 4.5V$	26		





lo	D	٧	lev

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Limit	Units		
Drain-Source Voltage			60	V	
Gate-Source Voltage	$V_{GS}$	±20	V		
Continuous Drain Current <sup>a</sup>	$T_C=25^{\circ}C$	$I_D$	19	_	
Pulsed Drain Current <sup>b</sup>			40	Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	30	A		
Power Dissipation <sup>a</sup>	$T_C=25^{\circ}C$	$P_{\mathrm{D}}$	50	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ heta JA}$	50	°C/W	
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W	

1

### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

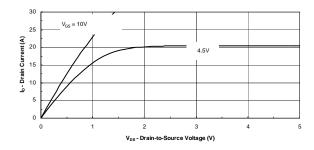
_		SS OTHERWISE NOTED)	Limits				
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1.0			V	
Gate-Body Leakage	Igss	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA	
Zana Cata Valtaga Duain Cumant	Ingg	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	A	
Zero Gate Voltage Drain Current	Idss	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			A	
D i G O D i A		$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$			38	mΩ	
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 26 \text{ A}$			50	IILZ	
Forward Tranconductance <sup>A</sup>	gs	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$		22		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 24 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	V 15 V V 4 5 V		12.5			
Gate-Source Charge	Qgs	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 30 \text{ A}$		2.4		nC	
Gate-Drain Charge	Qgd	ID = 30  A		2.6			
Turn-On Delay Time	t <sub>d(on)</sub>			11			
Rise Time	tr	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 30 \text{ A},$		8		C	
Turn-Off Delay Time	td(off)	$V_{GEN} = 10 \text{ V}$		19		nS	
Fall-Time	$t_{\mathrm{f}}$			6			

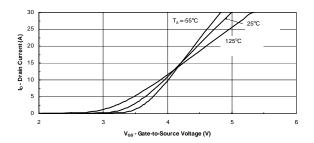
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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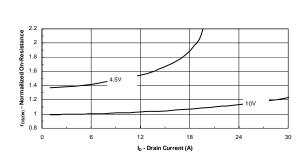
# Typical Electrical Characteristics

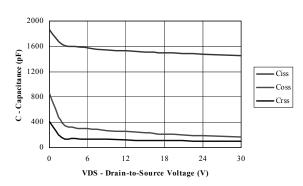




**Output Characteristics** 

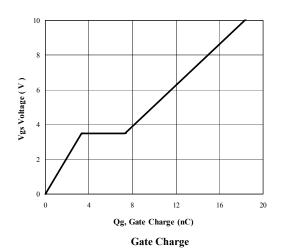
**Transfer Characteristics** 

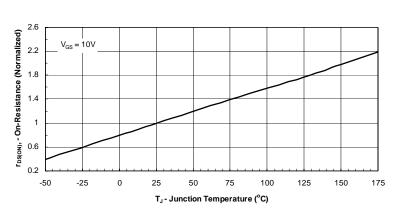




On-Resistance vs. Drain Current

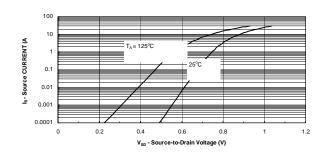
Capacitance

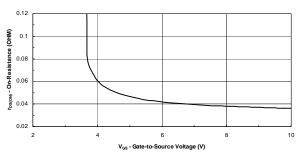




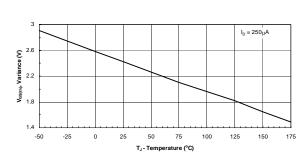
On-Resistance vs. Junction Temperature

## Typical Electrical Characteristics (N-Channel)

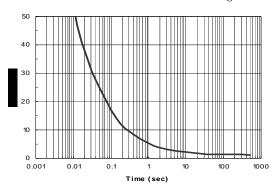




Source-Drain Diode Forward Voltage

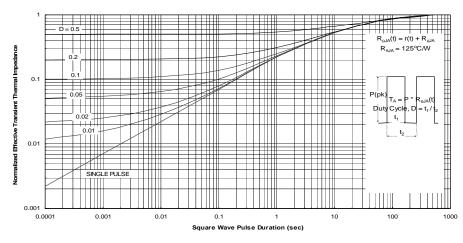


On-Resistance vs.Gate-to Source Voltage



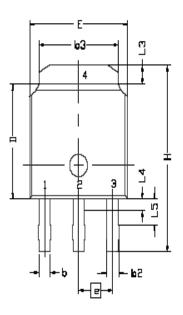
Threshold Voltage

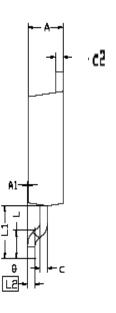
Single Pulse Power

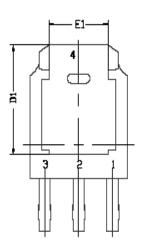


Normalized Thermal Transient Impedance, Junction-to-Ambient

# Package Information







DIMENS:	IUNAL I	(FRW) 7
MIN	M	MAX
6.40	6.60	6.731
1,40	152	1.77
		EF
Ģ	508 BS	
0.89	•	1.27
0.64	I	1.01
!	-	-
6,00	6,10	6.223
9.40	10.00	10.40
0.64	0.76	0.88
0.77	0.84	1.14
5,21	5,34	5.46
2	206 BS	
2.20	2.30	5:38
0.00	i	0.127
0.45	0.50	0,60
0,45	050	0.58
5.30		
4.40		
Q*		10*
	6.40 1.40 0.89 0.64 	MIN NOM  6.40 6.60  1.40 1.52  2.743 R  0.508 BS  0.89  0.64   6.00 6.10  9.40 10.00  0.64 0.76  0.77 0.84  5.21 5.34  2.286 BS  2.20 2.30  0.45 0.50  0.45 0.50  0.45 0.50  5.30  4.40

DIMENSIONAL DECOMES